

IN THE SPECIFICATION

a' Delete the title and insert Trenched Gate Non-Volatile Semiconductor Method With the Source/Drain Regions Spaced From the Trench by Sidewall Dopings

Amend the specification by inserting immediately after the the section titled RELATED APPLICATIONS:

a'' ~This is a divisional of co-pending application Serial No. 09/052,057 filed on March 30, 1998, which is incorporated by reference herein in its entirety.~

Kindly amend:

Page 1, lines ⁸⁻⁹~~9-10~~, delete "Ser. No. _____," and insert -- Ser. No. 09/052,051,--;

and

a³ Page 1, line ⁹~~10~~, delete the first occurrence of " '[TITLE]' " and insert "A Trenched Gate Metal Oxide Semiconductor Device and Method"~;

a⁴ Page 1, line ⁹~~10~~, after the first occurrence of " '[TITLE]' " please insert Ser. No. 09/052,058, "Trenched Gate Semiconductor Device and Method for Low Power Applications"~;

Page 1, line ⁹~~10~~, delete the second occurrence of "Ser. No. _____," and insert -- Ser. No. 09/052,062, --; and

a⁵ Page 1, line ⁹~~10~~, delete the second occurrence of " '[TITLE]' " and insert "A Trenched Gate Non-Volatile Semiconductor Device and Method With Corner Doping and Sidewall Doping"~.

IN THE CLAIMS:

Please cancel claims 1-15.